



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C		
	4.0Ω @ V _{GS} = 10V	247mA		
60V	4.1Ω @ V _{GS} = 5V	244mA		
	5.0Ω @ V _{GS} = 4V	221mA		

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
- https://www.diodes.com/quality/product-definitions/

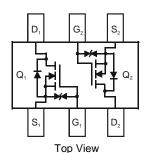
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Alloy42 Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (Approximate)





Top View



Internal Schematic

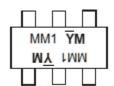
Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002DWS-7	SOT363	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



MM1 = Product Type Marking Code YM = Date Code Marking \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	202	1 2	2022	2023	2024	202	25 2	2026	2027
Code	F	G	Н	- 1		J	K	L	М		N	0
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	247 198	mA	
Maximum Body Diode Forward Current (Note 6)		Is	247	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)	I _{DM}	1.8	Α
Pulsed Source Current (10µs Pulse, Duty Cycle =	1%)	I _{SM}	1.8	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P _D	0.29	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	438	°C/W
Total Power Dissipation (Note 6)		P _D	0.37	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	341	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	1	1.0	μΑ	$V_{DS} = 60V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.0		2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
			1.89	4.0		$V_{GS} = 10V, I_D = 0.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		1.85 1.97	4.1	Ω	$V_{GS} = 5V, I_D = 0.2A$	
				5.0		$V_{GS} = 4V, I_D = 0.2A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.1	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	41	_	pF	V 051/ 1/ 01/	
Output Capacitance	Coss	_	4.4	_	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	2.6	_	рF	1 - 1.000112	
Gate Resistance	R_{g}	_	900	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$	
Total Gate Charge	Qg	_	0.4		nC	45)/ // 40)/	
Gate-Source Charge	Q_{gs}	_	0.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250mA$	
Gate-Drain Charge	Q_{gd}	_	0.1		nC	ID = 250MA	
Turn-On Delay Time	t _{D(ON)}	_	3.7	_	ns		
Turn-On Rise Time	t _R	_	3.6	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	102	_	ns	$R_g = 25\Omega$, $I_D = 200 \text{mA}$	
Turn-Off Fall Time	t _F	_	22	_	ns		
Reverse Recovery Time	t _{RR}	_	20	_	ns	I _F = 1A, di/dt = 100A/μs	
Reverse Recovery Charge	Q_{RR}	_	7.9	_	nC	I _F = 1A, di/dt = 100A/μs	

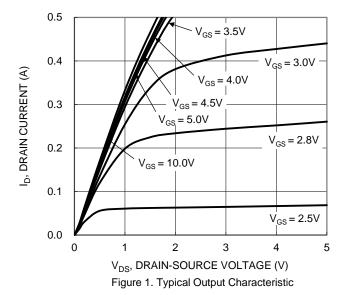
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

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^{6.} Device mounted on 1" \times 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.





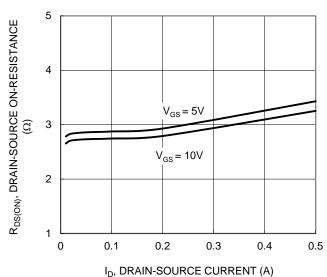


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

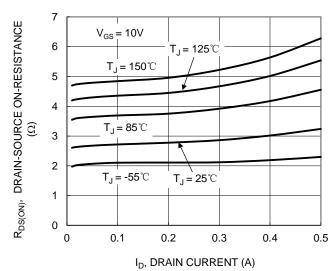


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

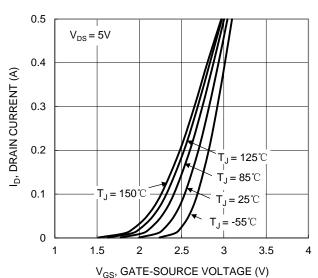
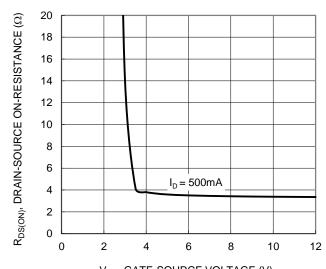
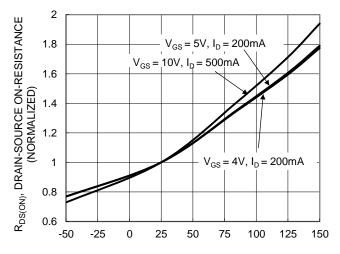


Figure 2. Typical Transfer Characteristic



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic



 T_J , JUNCTION TEMPERATURE ($^{\circ}$ C) Figure 6. On-Resistance Variation with Junction Temperature



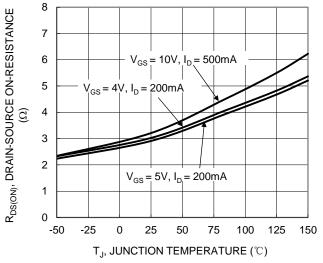
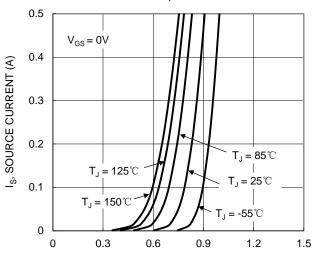


Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

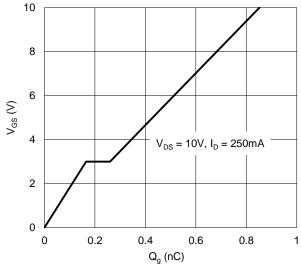


Figure 11. Gate Charge

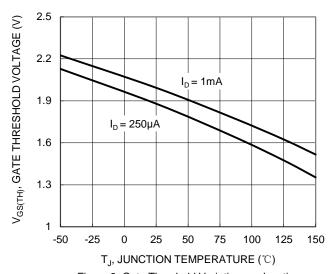


Figure 8. Gate Threshold Variation vs. Junction Temperature

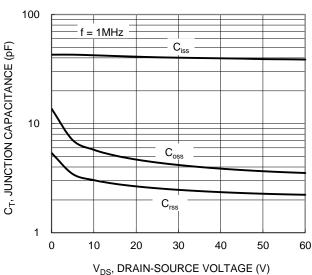


Figure 10. Typical Junction Capacitance

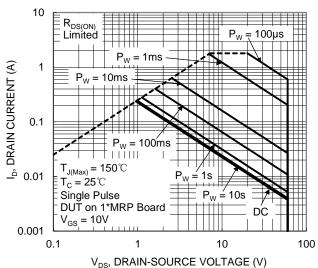


Figure 12. SOA, Safe Operation Area



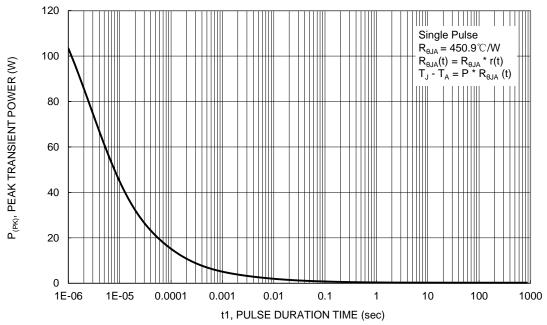


Figure 13. Single Pulse Maximum Power Dissipation

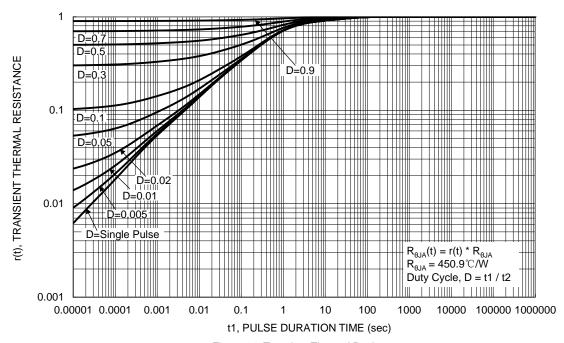


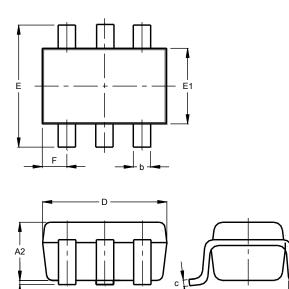
Figure 14. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363

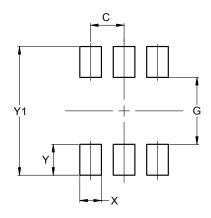


SOT363								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.10	0.30	0.25					
С	0.10	0.22	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C).650 E	SC					
F	0.40	0.45	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
V1	2 500



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